

## Editorial Preface

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Since the mid-1990s III-V nitride semiconductors are promising materials for optoelectrical devices in the short-wavelength and visible spectral range. The market for such products already exists and corresponds to large production values. Other applications are still under development the most important one being the high power-high frequency electronics.

This Symposium on 'Group III Nitrides' at the 2000 Spring Meeting of the European Materials Research Society in Strasbourg, France, enjoyed a truly international attendance. The number of accepted papers has reached 110 in 2000. The purpose of the conference was to provide a forum for discussions on the progress made in the entire field from growth, characterization to processing and devices of nitride material. This includes many fundamental issues, still unsolved device issues and improvements in device reliability.

This special issue of *Materials Science and Engineering B* brings together qualified papers which have been reviewed and evaluated keenly. In total there are 78 papers demonstrating the current and advanced achievement in nitride semiconductors.

We would like to thank the Scientific Committee for setting up an excellent and balanced program and all the reviewers for their careful reading and scientific evaluation of these papers. We, also, would like to thank Aixtron and Emcore. Their generous support contributed a lot to the success of the meeting.

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